# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

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We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

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Taiwan Semiconductor

### N-Channel Power MOSFET

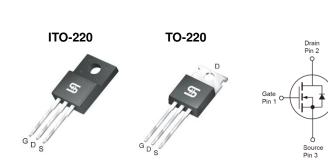
600V, 18A, 0.19Ω

#### FEATURES

- Super-Junction technology
- High performance, small  $R_{DS(ON)}^{*}Q_{g}$  figure of merit (FOM)
- High ruggedness performance
- 100% UIS tested
- High commutation performance
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

#### APPLICATIONS

- Power Supply
- AC/DC LED Lighting



<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER		SYMBOL	ITO-220	<b>TO-220</b>	UNIT	
Drain-Source Voltage		$V_{\text{DS}}$	600		V	
Gate-Source Voltage		$V_{GS}$	±30		V	
Continuous Drain Current (Note 1)	$T_{\rm C} = 25^{\circ}{\rm C}$	- I <sub>D</sub>	18		А	
	$T_{C} = 100^{\circ}C$		10.8		А	
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	54		А	
Total Power Dissipation @ $T_c = 25^{\circ}C$		P <sub>DTOT</sub>	33.8	150.6	W	
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	212.9		mJ	
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	2.6		А	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150		°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	ITO-220	<b>TO-220</b>	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	3.7	0.83	°C/W	
Junction to Ambient Thermal Resistance	R <sub>OJA</sub>	62		°C/W	

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air.

KEY PERFORMANCE PARAMETERS				
PARAMETER VALUE UNIT				
V <sub>DS</sub>	600	V		
R <sub>DS(on)</sub> (max)	0.19	Ω		
Qg	31	nC		



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ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV <sub>DSS</sub>	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V <sub>GS(TH)</sub>	2.0	3.0	4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Drain-Source On-State Resistance (Note 4)	$V_{GS} = 10V, I_D = 6A$	R <sub>DS(on)</sub>		0.17	0.19	Ω
Dynamic (Note 5)	l		1		1	I
Total Gate Charge	$V_{DS} = 380V, I_D = 18A,$	Qg		31		nC
Gate-Source Charge		Q <sub>gs</sub>		8		
Gate-Drain Charge	$V_{GS} = 10V$	Q <sub>gd</sub>		12.6		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C <sub>iss</sub>		1273		-
Output Capacitance	f = 1.0MHz	C <sub>oss</sub>		92		pF
Gate Resistance	F = 1MHz, open drain	R <sub>g</sub>		3.1		Ω
Switching (Note 6)	·					
Turn-On Delay Time		t <sub>d(on)</sub>		36		
Turn-On Rise Time	$V_{DD} = 380V,$ $R_{GEN} = 25\Omega,$ $I_D = 18A, V_{GS} = 10V,$	tr		21		
Turn-Off Delay Time		t <sub>d(off)</sub>		95		ns
Turn-Off Fall Time	$I_D = IOA, V_{GS} = IOV,$	t <sub>f</sub>		21		
Source-Drain Diode	·					•
Forward On Voltage (Note 4)	$I_{\rm S} = 18$ A, $V_{\rm GS} = 0$ V	V <sub>SD</sub>			1.4	V
Reverse Recovery Time	V <sub>B</sub> =100V, I <sub>S</sub> = 18A	t <sub>rr</sub>		359.4		ns
Reverse Recovery Charge	$dI_{F}/dt = 100A/\mu s$	Q <sub>rr</sub>		4.54		μC

Notes:

1. Current limited by package.

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2. Pulse width limited by the maximum junction temperature.

3. L = 63mH, I\_{AS} = 2.6A, V\_{DD} = 50V, R\_G = 25 $\Omega$ , Starting T\_J = 25°C

4. Pulse test: PW  $\leq$  300µs, duty cycle  $\leq$  2%.

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.

#### **ORDERING INFORMATION**

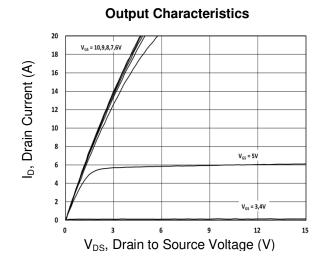
PART NO.	PACKAGE	PACKING
TSM60NB190CI C0G	ITO-220	50pcs / Tube
TSM60NB190CZ C0G	TO-220	50pcs / Tube



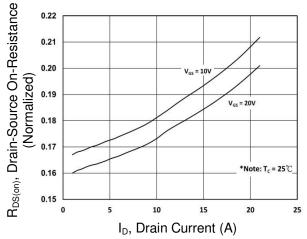
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#### CHARACTERISTICS CURVES

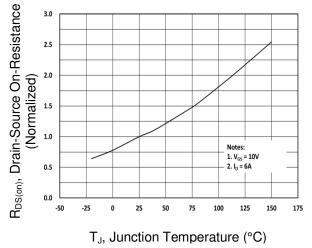
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 



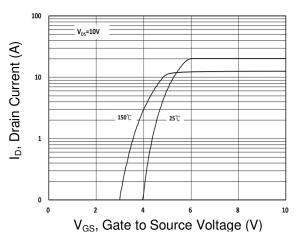
On-Resistance vs. Drain Current



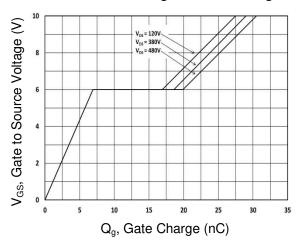




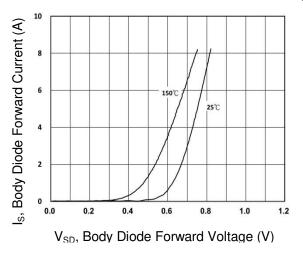
**Transfer Characteristics** 



Gate-Source Voltage vs. Gate Charge



Source-Drain Diode Forward Current vs. Voltage

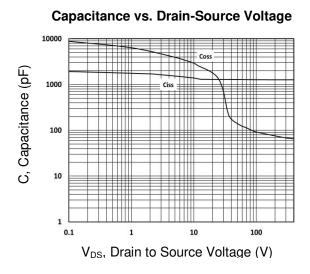




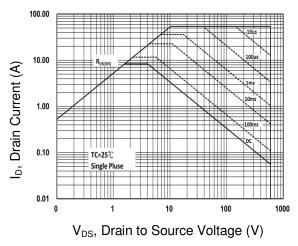
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### CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

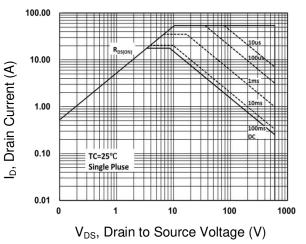


Maximum Safe Operating Area (ITO-220)

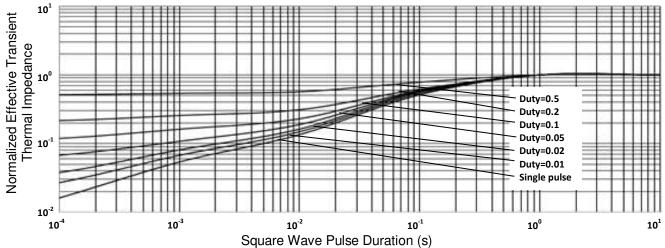


BV<sub>DSS</sub> vs. Junction Temperature 1.15 BV<sub>DSS</sub> (Normalized) Drain-Source Breakdown Voltage 1.10 1.05 1.00 Notes: 1. V<sub>GS</sub> = 0V 2. I<sub>D</sub> = 0.25mA 0.95 0.90 -50 -25 25 50 75 100 125 150 175 0 T<sub>J</sub>, Junction Temperature (°C)

Maximum Safe Operating Area (TO-220)

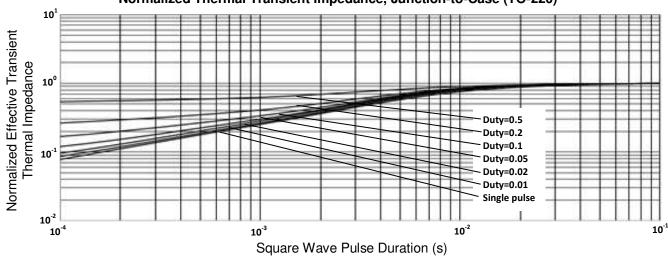








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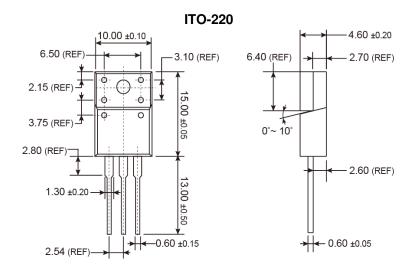
#### Normalized Thermal Transient Impedance, Junction-to-Case (TO-220)

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### TSM60NB190CI TSM60NB190CZ

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#### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



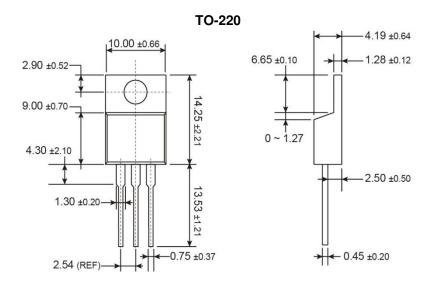
#### **MARKING DIAGRAM**

- 0 0 0 0 TSC 80NB190 GYWWF #1
- **G** = Halogen Free
- Y = Year Code
- WW = Week Code (01~52)
  - **F** = Factory Code



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### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



#### **MARKING DIAGRAM**

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